L Number	Hits	Search Text	DB	Time stamp
-	0	("nmos near capacitor").PN.	USPAT;	2003/04/20
			US-PGPUB	15:39
-	157	nmos near capacitor	USPAT;	2003/04/20
	 2568	\$1mos near capacitor	US-PGPUB USPAT;	2003/04/20
] -	2500	\$1mos near capacitor	US-PGPUB	16:28
1_	52	(\$1mos near capacitor) and (low\$1pass	USPAT;	2003/04/20
		near filter)	US-PGPUB	16:42
-	426	257/288.ccls.	USPAT;	2003/04/20
	-10	057/060 1 057/000 1	US-PGPUB	17:13
-	516	257/368.ccls. not 257/288.ccls.	USPAT; US-PGPUB	2003/04/20
_	799	257/532.ccls. not (257/368.ccls.	USPAT;	2003/04/20
		257/288.ccls.)	US-PGPUB	18:07
-	82	(257/532.ccls. 257/595.ccls.	USPAT;	2003/04/20
		257/601.ccls.) and (\$1mos near	US-PGPUB	18:32
		capacitor\$1)		2002/04/20
-	80	438/379.ccls.	USPAT; US-PGPUB	2003/04/20 18:15
_	77	438/394.ccls.	USPAT;	2003/04/20
	''	10,001.001.	US-PGPUB	18:15
-	22	(438/197.ccls. 438/381.ccls.) and (\$1mos	USPAT;	2003/04/20
		near capacitor\$1)	US-PGPUB	18:35
-	356	438/307.ccls.	USPAT;	2003/04/20
	248	327/558.ccls.	US-PGPUB USPAT;	18:46 2003/04/20
-	248	327/558.CCIS.	US-PGPUB	18:52
_	368	327/157.ccls. not 327/558.ccls.	USPAT;	2003/04/20
			US-PGPUB	18:52
-	10151	(gate with (p\$1type boron)) and ((source	USPAT;	2003/04/20
	0000	drain) with (p\$1type boron))	US-PGPUB	19:21
_	8023	((gate with (p\$1type boron)) and ((source drain) with (p\$1type boron))) and ((gate	USPAT; US-PGPUB	2003/04/20
		with (p\$1type boron)) same ((source	05 10105	15.21
		drain) with (p\$1type boron)))		
-	1273	(((gate with (p\$1type boron)) and	USPAT;	2003/04/20
		((source drain) with (p\$1type boron)))	US-PGPUB	19:22
		and ((gate with (p\$1type boron)) same ((source drain) with (p\$1type boron))))		
		and p\$1well		
_	54		USPAT;	2003/04/20
		((source drain) with (p\$1type boron)))	US-PGPUB	19:36
		and ((gate with (p\$1type boron)) same		
		((source drain) with (p\$1type boron))))		
_	3	and p\$1well) and (\$1mos near capacitor) (polysilicon near capacitor) same	USPAT	2003/04/20
		(electrode\$1 with (p\$type boron))		19:38
-	6	(polysilicon near capacitor) same	USPAT	2003/04/20
		(electrode\$1 with (p\$1type boron))		19:39
- '	1146	capacitor near \$1mos	EPO; JPO; DERWENT;	2003/04/20
			IBM TDB	19.40
-	29	(capacitor near \$1mos) and (gate with	EPO; JPO;	2003/04/20
		(p\$1type boron))	DERWENT;	19:50
			IBM_TDB	0000/01/00
-	555	(gate near p\$1type) and mos	USPAT	2003/04/20
_	323	((gate near p\$1type) and mos) and (gate	USPAT	2003/04/20
	323	near (n\$1type))	,	19:52
-	191	(((gate near p\$1type) and mos) and (gate	USPAT	2003/04/20
		near (n\$1type))) and ((gate near n\$1type)		20:11
		with (gate near p\$1type))		2002/04/22
-	223	capacitor with p\$1type with (diffusion implant\$7)	USPAT	2003/04/20
_	15	I	USPAT	2003/04/20
		implant\$7)) same (p\$1type with (upper		20:14
		top))		
-	0		USPAT	2003/04/20
L	L	electrode))		20:22

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-	0 capacitor same (p\$1type near (upper adj	USPAT	2003/04/20	٦
	electrode))		20:23	-
_	0 capacitor and (p\$1type near (upper adj	USPAT	2003/04/20	
	electrode))		20:23	
-	2 capacitor and (p\$1type near (top adj	USPAT	2003/04/20	
	electrode))		20:23	